# NSN 5962-01-444-6546

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# Maximum Power Dissipation Rating:

1.0 watts

#### **Operating Tempurature Range:**

-55.0/+125.0 degrees celsius

# Storage Tempurature Range:

-65.0/+150.0 degrees celsius

### **End Application:**

F-15i

## **Features Provided:**

Electrostatic sensitive and monolithic and static operation

#### **Inclosure Material:**

Silicon

#### **Inclosure Configuration:**

Dual-in-line

#### **Output Logic Form:**

Complementary-metal oxide-semiconductor logic

#### **Criticality Code Justification:**

Cbbl

## **Current Rating Per Characteristic:**

15.00 milliamperes forward current, peak total value not applicable

## **Terminal Surface Treatment:**

Solder

#### **Product Name:**

Microcircuit, memory, digital, cmos, 2k x 8 non-volatile static ram, monolithic silicon

#### Voltage Rating And Type Per Characteristic:

-0.6 volts total supply and 7.0 volts total supply

#### Time Rating Per Chacteristic:

55.00 nanoseconds access

#### Memory Device Type:

Ram

#### **Special Features:**

Descriptive designator cdip3-t28 or gdip4-t28; circuit function 8k x 8 nvsram

#### Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

#### **Terminal Type And Quantity:**

28 printed circuit

#### Shelf Life:

N/a

#### Unit Of Measure:

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## Demilitarization:

No

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